

ABSTRACT OF THE DISCLOSURE

A manufacturing method for a bipolar gate CMOS semiconductor device is provided that eliminates a masking process for P-type polycrystalline silicon. An N-type polycrystalline silicon region is selectively formed in polycrystalline silicon constituting a gate electrode through predeposition using an insulating film as a mask, after which the insulating film is removed to implant P-type impurity ions into the entire surface to form a P-type polycrystalline silicon region.